

Docket No. 210136US99



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Ravindranath DROOPAD, et al.

SERIAL NO: 09/901,109

GAU: 2815

FILED: July 10, 2001

EXAMINER: BAUMEISTER

FOR: STRUCTURE AND METHOD FOR FABRICATING SEMICONDUCTOR STRUCTURES AND DEVICES UTILIZING THE FORMATION OF A COMPLIANT SUBSTRATE COMPRISING AN OXYGEN-DOPED COMPOUND SEMICONDUCTOR LAYER

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references were submitted in application Serial No. 09/908,888 according to the attached copy of a Granted Petition. This application contains related subject matter.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

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Respectfully submitted,

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MAIER & NEUSTADT, P.C.

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Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

LIST OF REFERENCES CITED BY APPLICANT

ATTY DOCKET NO.
210136US99SERIAL NO.
09/901,109

APPLICANT

Ravindranath DROOPAD, et al.

FILING DATE

July 10, 2001

GROUP

2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
XN	6,233,435 B1	05/15/01	WONG			
XO	4,723,321	02/02/88	SALEH			
XP	6,181,920 B1	01/30/01	DENT ET AL			
XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
XR	5,760,740	06/02/98	BLODGETT			
XS	5,238,877	08/24/93	RUSSELL			
XT	4,876,218	10/24/89	PESSA ET AL			
XU	6,232,242 B1	05/15/01	HATA ET AL			
XV	4,378,259	03/29/83	HASEGAWA ET AL			
XW	6,278,541 B1	08/21/01	BAKER			
XY	4,298,247	11/03/81	MICHELET ET AL			
XZ	4,174,504	11/13/79	CHENAUSKY ET AL			
YA	3,758,199	09/11/73	THAXTER			
YB	6,362,558 B1	03/26/02	FUKUI			
YC	6,140,746	10/31/00	MIYASHITA ET AL			
YD	2002/0076878 A1	06/20/02	WASA ET AL			
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YF	2002/0179000 A1	12/05/02	LEE ET AL			
YG	6,341,851	01/29/02	TAKAYAMA ET AL			
YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
YI	6,204,525 B1	03/20/01	SAKURAI ET AL			
YJ	5,985,404	11/16/99	YANO ET AL			
YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
YL	6,498,358 B1	12/24/02	LACH ET AL			
YM	5,387,811	02/07/95	SAIGOH			
YN	5,523,602	06/04/96	HORIUCHI ET AL			
YO	5,362,998	11/08/94	IWAMURA ET AL			
YP	5,188,976	02/23/93	KUME ET AL			
Examiner				Date Considered		

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 210136US99		SERIAL NO. 09/901,109	
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		U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS
	YQ	6,501,121 B1	12/31/02	YU ET AL	
	YR	5,919,515	07/06/99	YANO ET AL	
	YS	5,238,877	08/24/93	RUSSELL	
	YT	5,540,785	07/30/96	DENNARD ET AL	
	YU	5,997,638	12/07/99	COPEL ET AL	
	YV	6,291,866	09/18/01	WALLACE	
	YW	5,365,477	11/15/94	COOPER, JR ET AL	
	YX	5,548,141	08/20/96	MORRIS ET AL	
	YY	2002/0021855	02/21/02	KIM	
	YZ	6,110,840	08/29/00	YU	
	ZA	5,667,586	09/16/97	EK ET AL	
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL	
	ZC	5,315,128	05/24/94	HUNT ET AL	
	ZD	5,919,522	07/06/99	BAUM ET AL	
	ZE	4,843,609	06/27/89	OHYA ET AL	
	ZF	4,626,878	12/02/86	KUWANO ET AL	
	ZG	4,525,871	06/25/85	FOYT ET AL	
	ZH	3,818,451	06/18/74	COLEMAN	
	ZI	6,059,895	05/09/00	CHU ET AL	
	ZJ	4,447,116	05/08/84	KING ET AL	
	ZK	6,022,671	02/08/00	BINKLEY ET AL	
	ZL	5,754,714	05/19/98	SUZUKI ET AL	
	ZM	6,524,651 B2	02/25/03	GAN ET AL	
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL	
	ZO	5,642,371	06/24/97	TOHYAMA ET AL	
	ZP	6,445,724 B2	09/03/02	ABELES	
	ZQ	5,753,934	05/19/98	YANO ET AL	
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL	
	ZS	6,051,874	04/18/00	MASUDA	
	ZT	5,166,761	11/24/92	OLSON ET AL	
	ZU	5,574,744	11/12/96	GAW ET AL	
Examiner _____				Date Considered _____	

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Form PTO 1449 (Modified)		U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 210136US99	SERIAL NO. 09/901,109
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Ravindranath DROOPAD, et al.			
		FILING DATE July 10, 2001	GROUP 2815		
FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT		
CCB	2 152 315	07/31/85	GREAT BRITAIN		
CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)		
CCE	WO 03/012874	02/13/03	WIPO		
CCF	1 043 427	10/11/00	EUROPE		
CCG	1 069 605	01/17/01	EUROPE		
CCH	WO 02/099885	12/12/02	WIPO		
CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT		
CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)		
CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)		
CCL	WO 02/11254	02/07/02	WIPO		
CCM	0 494 514	07/15/92	EUROPE		
CCN	0 247 722	12/02/87	EUROPE		
CCO	1 037 272	09/20/00	EUROPE		
CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)		
CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT		
CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT		
CCS	0 392 714	10/17/90	EUROPE		
CCT					
CCU					
CCV					
CCW					
CCX					
CCY					
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CDA					
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		FILING DATE July 10, 2001	GROUP 2815	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)				
LLAA	Peter Weiss: "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3			
LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001			
LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3			
LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3			
LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO ₃ Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651			
LLAF	V. Bornand et al.; "Deposition of LiTaO ₃ thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244			
LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296			
LLAH	A.K. Sharma et al.; "Integration of Pb(Zr0.52Ti0.48)O ₃ epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460			
LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 Ieee Electron Device Letters; 12(1991) September, No. 9, New York, US			
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LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287			
LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958			
LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246			
LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO ₃ at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169			
LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536			
LLAP				
LLAQ				
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